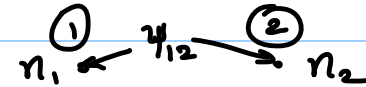


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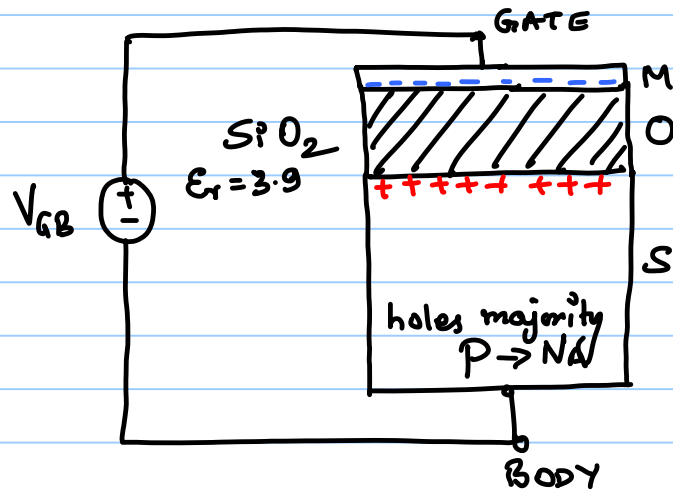
MODULE 1: THE TRANSISTOR

- 1) LAW OF MASS ACTION: $n_p = n_i^2 (e^{q\psi_2/kT})$
- 2) MAXWELL-BOLTZMANN LAW: $n_1/n_2 = e^{q\psi_{12}/kT}$
- 3) $W_N N_D = W_P N_A \Rightarrow N_D \gg N_A \Rightarrow W_P \gg W_N$



MOS CAPACITOR

MOS \rightarrow METAL OXIDE SEMICONDUCTOR

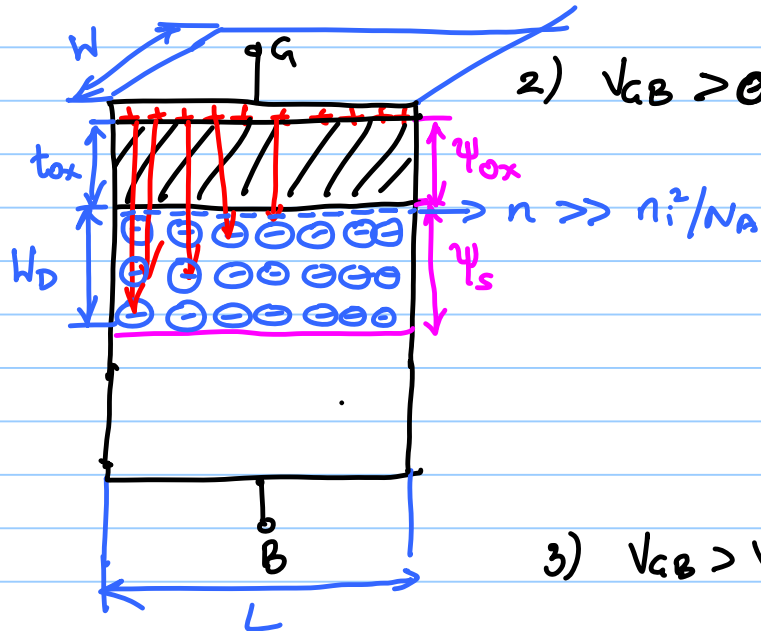


$NA \rightarrow$ BORON CONC $10^{15}/cm^2$

$$p = N_A$$
$$n = n_i^2 / N_A$$

1) $V_{GB} < 0 \rightarrow$ ACCUMULATION

2) $V_{GB} > 0$



2) $V_{GB} > 0 \rightarrow$ DEPLETION

$$n_s = n_B e^{\frac{q\psi_s}{kT}}$$

$$\psi_s = \frac{kT}{q} \ln \left(\frac{n_s}{n_B} \right)$$

PINNED \rightarrow When $n_s = N_A$

3) $V_{GB} > V_{TH} \rightarrow$ INVERSION

$$\psi_s = \frac{kT}{q} \ln \left(\frac{N_A}{n_i^2 / N_A} \right) = 2 \frac{kT}{q} \ln \left(\frac{N_A}{n_i^2} \right)$$

$$\boxed{\psi_s = 2 \frac{kT}{q} \ln \left(\frac{N_A}{n_i^2} \right)}$$

$V_{TH} \rightarrow$ THRESHOLD VOLTAGE \rightarrow GATE POTENTIAL NEEDED TO "INVERT" THE SURFACE

$$V_{GB} = \psi_s + \psi_{ox}$$

$$\psi_{ox} = -\frac{(Q'_D + Q'_I)}{C_{ox}}$$

$$C_{ox} = \frac{\epsilon_r \epsilon_0 W L}{t_{ox}} \rightarrow C_{ox} = \frac{\epsilon_r \epsilon_0}{t_{ox}}$$

$Q'_D, Q'_I \rightarrow$ charge

$Q_D, Q_I \rightarrow$ charge per unit area.

$$Q'_D = q \cdot N_A \cdot (W L \cdot W_D)$$

$$W_D = \sqrt{\frac{2 \epsilon_s \epsilon_i |\psi_s|}{q N_A}}$$

$$\Rightarrow Q'_D = q N_A (W L \cdot \sqrt{\frac{2 \epsilon_s \epsilon_i |\psi_s|}{q N_A}})$$

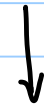
$$\Rightarrow Q_D' = \left(\sqrt{2\epsilon_{si} |\psi_s| q N_A} \right) WL$$

$$\Rightarrow Q_D = \sqrt{2\epsilon_{si} |\psi_s| q N_A}$$

$$V_{GB} = \left(\psi_s - \frac{Q_D'}{C_{ox}'} \right) - \frac{Q_I'}{C_{ox}'}$$

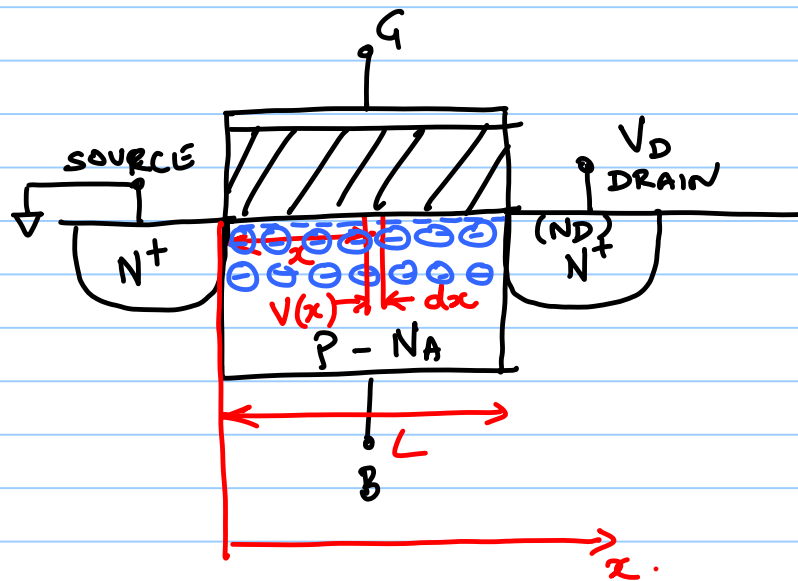
$$Q_I' = -C_{ox}' (V_{GB} - V_{TH})$$

$$V_{TH} = \psi_s - \frac{1}{C_{ox}'} \cdot \sqrt{2\epsilon_{si} |\psi_s| q N_A}$$



$$\epsilon_{rsi} \epsilon_0.$$

MOS TRANSISTOR



$N^+ \rightarrow$ N-TYPE SEMI COND WITH
LARGE DOPING ($N_D \sim 10^{17} - 10^{19} \text{ cm}^{-3}$)

$$V(0) = 0$$

$$V(L) = V_D$$

$$Q_I = -C_{ox}(V_G - V_T - V)$$

$$dQ'_I = Q_I \cdot W dx$$

$$I_D \leftarrow \frac{dQ'_I}{dt} = -C_{ox}(V_G - V_T - V) \cdot W \frac{dx}{dt}$$

$\rightarrow v_d$ (drift velocity)

$$\therefore I_D = -C_{ox} (V_G - V_T - V) v_d \cdot W$$

$$v_d = \mu_n E$$

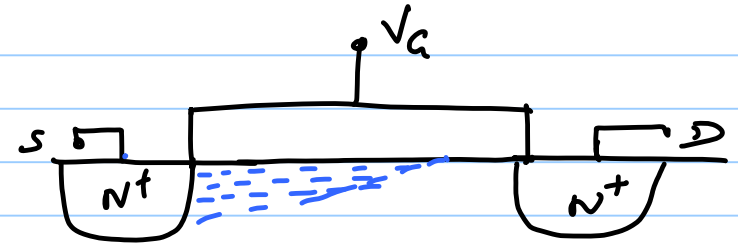
$$= -\mu_n \frac{dV}{dx}$$

$$\therefore \int_0^L I_D dx = \int_0^{V_D} \mu_n C_{ox} W (V_G - V_T - V) dV$$

$$\therefore I_D \cdot L = \mu_n C_{ox} W \left[(V_G - V_T) V_D - \frac{V_D^2}{2} \right]$$

$$\therefore I_D = \mu_n C_{ox} \frac{W}{L} \left[(V_{GS} - V_T) V_{DS} - \frac{V_{DS}^2}{2} \right] \rightarrow \text{LINEAR}$$

$V_{DS} \uparrow$ at the source $(V_G - V_T) \rightarrow$ inversion
 Drain $(V_G - V_T - V_D)$



$$I_D = \mu_n C_{ox} \frac{W}{L} \left[(V_{GS} - V_T)(V_{GS} - V_T) - \frac{(V_{GS} - V_T)^2}{2} \right]$$

$$V_{GS} - V_T - V_{DS} > 0$$

$$V_{DS} < V_{GS} - V_T$$

$$= \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_T)^2 \rightarrow \text{SATURATION}$$